

STTH1506DPI

Tandem 600V HYPERFAST BOOST DIODE

MAJOR PRODUCTS CHARACTERISTICS

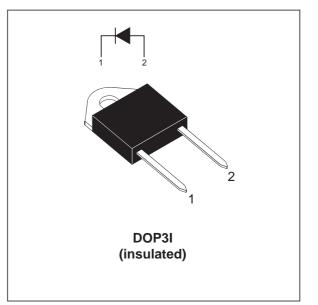
I _{F(AV)}	15 A
V _{RRM}	600 V
Tj (max)	150 °C
V _F (max)	2.4 V
I _{RM} (typ.)	4.8 A
t _{rr} (typ.)	16 ns

FEATURES AND BENEFITS

- ESPECIALLY SUITED AS BOOST DIODE IN CONTINUOUS MODE POWER FACTOR CORRECTORS AND HARD SWITCHING CONDITIONS
- DESIGNED FOR HIGH DI/DT OPERATION. HYPERFAST RECOVERY CURRENT TO COMPETE WITH SIC DEVICES. ALLOWS DOWNSIZING OF MOSFET AND HEATSINKS
- INTERNAL CERAMIC INSULATED DEVICES WITH EQUAL THERMAL CONDITIONS FOR BOTH 300V DIODES
- INSULATION (2500V_{RMS}) ALLOWS PLACEMENT ON SAME HEATSINK AS MOSFET AND FLEXIBLE HEATSINKING ON COMMON OR SEPARATE HEATSINK
- STATIC AND DYNAMIC EQUILIBRIUM OF INTERNAL DIODES ARE WARRANTED BY DESIGN

Maximum operating junction temperature

PACKAGE CAPACITANCE: C=16pF



DESCRIPTION

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high dI_F/dt .

Symbol	Parameter	Value	
V _{RRM}	Repetitive peak reverse voltage	600	
I _{F(RMS)}	RMS forward current		26
I _{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal	130
Ipeak	Peak current waveform	$\delta = 0.15$ Tc = 120°C	35
T _{stg}	Storage temperature range	4	-65 +150

ABSOLUTE RATINGS (limiting values)

Тj

Unit V A A A °C

°C

+ 150

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THERMAL AND POWER DATA

Symbol	Parameter	Test conditions	Value	Unit
R _{th (j-c)}	Junction to case		1.6	°C/W

STATIC ELECTRICAL CHARACTERISTICS (for both diodes)

Symbol	Parameter	Tests Conditions		Min.	Тур.	Max.	Unit
I _R *	Reverse leakage	$V_R = V_{RRM}$	Tj = 25°C			20	μA
	current		Tj = 125°C		30	200	
V _F **	Forward voltage drop	I _F = 15 A	Tj = 25°C			3.6	V
			Tj = 150°C		1.95	2.4	

Pulse test: * tp = 100ms, δ < 2%

** tp = 380 μ s, δ < 2%

To evaluate the maximum conduction losses use the following equation: P = 1.7 x $I_{F(AV)}$ + 0.047 x ${I_F}^2_{(RMS)}$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Tests Condition	Min.	Тур.	Max.	Unit	
t _{rr}	Reverse recovery time	$I_F = 0.5 \text{ A}$ $Irr = 0.25\text{ A}$ $I_R = 1 \text{ A}$	Tj = 25°C		16		ns
		I _F = 1 A dI _F /dt = - 50A/µs V _R = 30 V				35	
I _{RM}	Reverse recovery current	V _R = 400 V I _F = 15 A dI _F /dt = -200 A/µs	Tj = 125°C		4.8	6.0	A
S	Reverse recovery softness factor				0.4		-
Q _{rr}	Reverse recovery charges				80		nC

TURN-ON SWITCHING CHARACTERISTICS

Symbol	Parameter	Tests Conditions			Тур.	Max.	Unit
t _{fr}	Forward recovery time	$I_F = 15 \text{ A } dI_F/dt = 100 \text{A}/\mu\text{s},$ $V_{FR} = 1.1 \text{ x } V_F\text{max}$	Tj = 25°C			200	ns
V _{FP}	Forward recovery voltage	I _F = 15 A dI _F /dt = 100 A/µs	Tj = 25°C			6	V

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Fig. 1: Conduction losses versus average current.

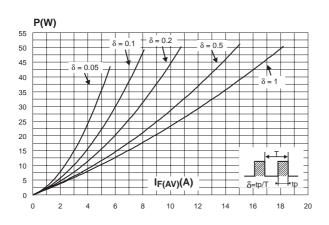


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration.

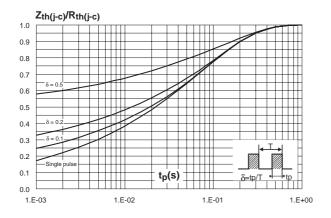
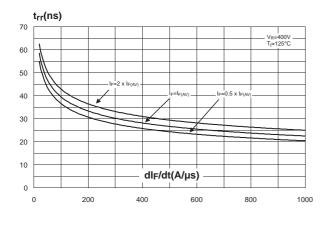
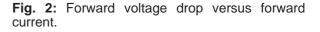


Fig. 5: Reverse recovery time versus dl_F/dt (typical values).



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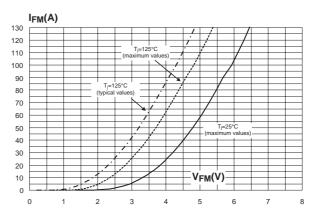


Fig. 4: Peak reverse recovery current versus dl_F/dt (typical values).

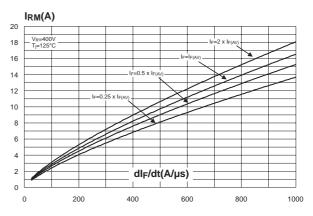
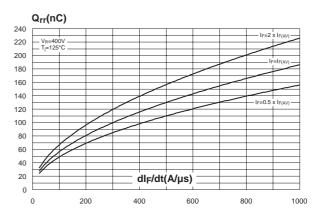


Fig. 6: Reverse recovery charges versus $dI_{F/dt}$ (typical values).



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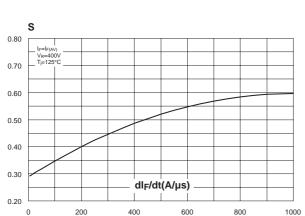


Fig. 7: Softness factor versus dI_F/dt (typical values).

Fig. 8: Relative variations of dynamic parameters versus junction temperature.

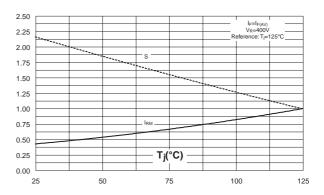


Fig. 9: Transient peak forward voltage versus dI_F/dt (typical values).

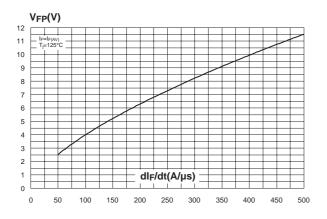


Fig. 11: Junction capacitance versus reverse voltage applied (typical values).

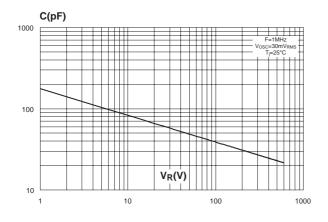
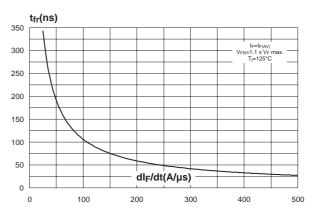
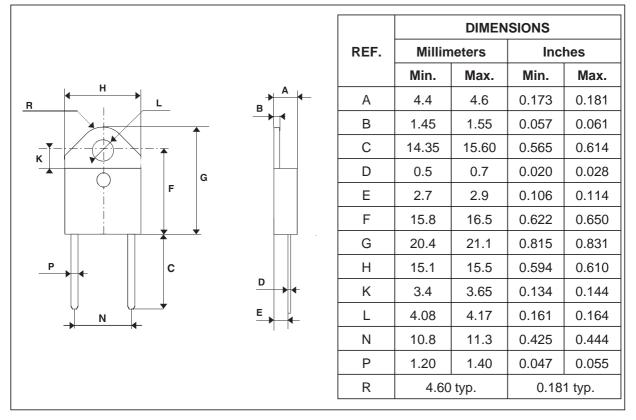


Fig. 10: Forward recovery time versus dI_F/dt (typical values).



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PACKAGE MECHANICAL DATA DOP3I



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH1506DPI	STTH1506DPI	DOP3I	4.46 g.	30	Tube

Epoxy meets UL94,V0

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